### THE UNITED STATES PATENT AND TRADEMARK OFFICE

Melvin K. CARTER

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Serial No.:

10/689,616

Art Unit:

To be assigned

Filed:

October 22, 2003

Examiner:

To be assigned

For:

**COMPOSITIONS FOR EXFOLIATION AGENT** EFFECTIVE IN REMOVING Attorney Docket No:

060937-0074-US

RESIST RESIDUES

#### TRANSMITTAL OF POWER OF ATTORNEY BY ASSIGNEE REVOKING PREVIOUS **POWERS OF RECORD**

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Sir:

Applicants' attorney encloses herewith a Revocation and Power of Attorney by Assignee for the above-identified application.

Please change the attorney docket number to 060937-0074-US. Future correspondence should be forwarded to Christopher G. Hayden, Customer No. 009629.

No fee is believed due at this time, however, the Commissioner is authorized to charge any fees associated with this communication to Morgan, Lewis & Bockius LLP Deposit Account No. 50-0310.

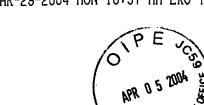
Respectfully submitted,

Christopher G. Havden

Date April 5, 2004

Customer Number 009629

Morgan, Lewis & Bockius LLP 1111 Pennsylvania Avenue, N.W. Washington, D.C. 20004 202-739-3001 (facsimile)



### REVOCATION AND POWER OF ATTORNEY

Commissioner for Patents P. O. Box 1450 Alexandria, Virginia 22313-1450

Sir:

EKC Technology, Inc., owner of the entire right, title and interest in, to and under the inventions described and claimed in the patent applications identified in the attached Schedule A, hereby revokes all previous powers of attorney and appoints Morgan, Lewis & Bockius LLP, Customer Number 009629, and each of them, its attorneys, to prosecute each of these patent applications, and to transact all business in the Patent and Trademark Office connected therewith.

Please direct all future correspondence to Customer No. 009629, Patent Support Unit, Morgan, Lewis & Bockius LLP, 1111 Pennsylvania Avenue, N.W., Washington, D.C. 20004, and direct all telephone calls to Morgan, Lewis & Bockius LLP at 202-739-3000.

Assignee:

EKC Technology, Inc.

Data: 29 March 2004

Signature:

Typed Name Michael A. Fury

Position/Title Vice President, R&D and Engineering

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App.#	sīde.	Jinventor(s)	Filing Date	New Attorney. Docket No. ■	Former Attorney Docket No.
	Compositions for Cleaning Organic				
	and Plasma Etched Residues for	·			
09/903,064	Semiconductor Devices	Small, et al.	07/10/2001	60937-091-US	8317-091-999
	Method of and Apparatus for				
09/874,330	Substrate Pre-Treatment	Maloney, et al.	06/06/2001	60937-111-US	8317-111-999
	Chemical Mechanical Polishing				
09/985,870	Compositions	Small, et al.	11/06/2001	60937-114-US	8317-114-999
•	Oxalic Acid as a Semiaqueous				
	Cleaning Product for Copper and			,	
10/421,706	Dielectrics	Lee, et al.	04/24/2003	60937-116-US	8317-116-999
	Sulfoxide Pyrolid(in)one Alkanolamine	1			
10/193,185	Cleaner Composition	Zhou, et al.	07/12/2002	60937-118-US	8317-118-999
	_				
	Method for the Deposition of Materials	1			
09/876,944	from Mesomorphous Films	Vasquez, et al.	06/08/2001	60937-120-US	8317-120-999
	Post Etch Cleaning Composition for				
10/007,134	Dual Damascene System	Payne, et al.	12/04/2001	60937-123-US	8317-123-999
	Photolytic Conversion Process to				
10/263,701	Form Patterned Amorphous Film	Bravo-Vasquez, et al.	10/04/2002	60937-126-US	8317-126-999
	Cleaning Solutions Including			<u> </u>	
	Nucleophilic Amine Compound				,
	Having Reduction and Oxidation				
09/988,545	Potential	Lee, et al.	11/20/2001	60937-127-US	8317-127-999
	Method and Compositions for				
	Chemically Treating A Substrate			-	
10/060,109	Using Foam Technology	Patel, et al.	01/28/2002	60937-129-US	8317-129-999
	Cleaning Solution Including				
	Nucleophilic Amine Compound				
10(105.005	Having Reduction and Oxidation		0.5/0.//0.000		
10/135,695	Potential	Lee, et al.	05/01/2002	60937-135-US	8317-135-999
10/448,127	Fluoride Layer and Removing Same	Melvin K. Carter	05/30/2003	60937-137-US	8317-137-999
	Process for the Use of Bis-Choline				
	and Tris-Choline in the Cleaning of				
	Quartz-Coated Polysilicon and Other				,
10/689,657	Materials	Charm, et al.	10/22/2003	60937-139-US	8317-139-999
	Cleaning Compositions Containing		•		
	Hydroxylamine Derivatives and				
	Process Using Same for Residue				
10/689,620	Removal	Zhou, et al.	10/22/2003	60937-140-US	8317-140-999
•					
10/005 515	Composition for Exfoliation Agent to	!			
10/689,616	be Used to Remove Resist Residues	Melvin K. Carter	10/22/2003	60937-141-US	8317-141-999
	Reducing Oxide Loss When Using			1	
	Fluoride Chemistries to Remove Post-				
00/407 404	Etch Residues in Semiconductor				
60/467,131	Processing	Lee, et al.	05/02/2003	60937-142-PR	8317-142-888

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EARSPPOTASE	Method for Depositing Patterned			abockethio1	∴≛Döcket No.
10/630,301	Films of Materials	Hill, et al.	07/30/2003	60937-143-US	8317-143-999
10.000,000	Methods for the Deposition of Silver			0000: 1:000	140 000
	and Silver Oxide Films and Patterned				
10/716,838	Films	Ruan, et al.	11/18/2003	60937-147-US	8317-147-999
	Semiconductor Process Residue			· · · · · · · · · · · · · · · · · · ·	
10/162,679	Removal Composition and Process	Lee, et al.	06/06/2002	60937-149-US	8317-149-999
	System and Method for Cleaning				
	Workpieces Using Supercritical				
60/469,826	Carbon Dioxide	Fury, et al.	05/13/2003	60937-150-PR	8317-150-888
		,	-		
	Abrasive-Free Chemical Mechanical	•			
40/000 040	Polishing Composition and Polishing		40/04/0000		
10/689,043	Process Containing Same	Yao, et al.	10/21/2003	60937-151-US	8317-151-999
10/689,042	Wet Etch of Titanium-Tungsten Film	Botol et el	10/21/2003	60027 450 116	9347 450 000
10/009,042	Wet Etch of Fitaniani-Tungsten Film	Patel, et al.	10/21/2003	60937-152-US	8317-152-999
	   Method of Depositing Nanostructured				
10/261,197	Films with Embedded Nanopores	Svendsen, et al.	09/30/2002	60937-153-US	8317-153-999
10/201,101	Hydrothermal Treatment of	· Ovoridoon, ot di.	00/00/2002	00007-100-00	0017-100-999
10/280,270	Nanostructured Films	Mukherjee, et al.	10/23/2002	60937-167-US	8317-167-999
10/257,469	Inhibition of Titanium Corrosion	Daviot, et al.	10/11/2002	60937-168-US	8317-168-999
	Chemical Mechanical Polishing				
10/401,405	Composition andProcess	Small, et al.	03/27/2003	60937-171-US	8317-171-999
	Aqueous Phosphoric Acid				
	Compositions for Cleaning				
10/688,900	Semiconductor Devices	Daviot, et al.	10/21/2003	60937-172-US	8317-172-999
	Load Lock System for Supercritical				
10/465,906	Fluid Cleaning	Fury, et al.	06/18/2003	60937-175-US	8317-175-999
40/405 005	Automated Dense Phase Fluid		00400000		·
10/465,905	Cleaning System Residue Removers for	Fury, et al.	06/18/2003	60937-176-US	8317-176-999
	Electrohydrodynamic Cleaning of		,		
60/455,439	Semiconductors	Robert J. Small	03/18/2003	60937-178-PR	8317-178-888
00/400,400	· · · · · · · · · · · · · · · · · · ·	Nobelt 3. Ollian	03/10/2003	00931-110-FIX	0317-170-000
	Free Radical-Forming Activator Attached to Solid and Used to				
10/361,822	Enhance CMP Formulations	Scott, et al.	02/11/2002	60937-179-US	0247 470 000
10/301,022	Titanium Carboxylate Films for Use in	Scott, et al.	02/11/2003	00937-179-05	8317-179-999
10/377,533	Semiconductor Processing	Hill, et al.	02/26/2003	60937-182-US	8317-182-999
10/422,860	Method of Making Barrier Layers	Maloney, et al.	05/20/2003	60937-183-US	8317-183-999
	Remover Formulation Containing		30,20,2000	33001 100 00	
	Fluoride for Use During				
60/463,739	Semiconductor Manufacturing	Hirasawa, et al.	04/18/2003	60937-185-PR	8317-185-888
	Cleaning Composition for Removing				
	Resists and Manufacturing Method of				
60/464,125	Semiconductor Devices	Hirasawa, et al.	04/21/2003	60937-186-PR	8317-186-888
	Deposition of Permanent Polymer				
10/422,212	Structures for OLED Fabrication	Roman, et al.	04/23/2003	60937-187-US	8317-187-999

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	. ⊤	inventor(s)	Filing	New Attorney	
жемер же	Seimconductor Process Residue	Y Zamveritor(s)	Date	Docket No.	Docket No.
10/442,858	Removal Composition and Process	Wai Mun Lee	05/20/2003	60937-189-US	9247 490 000
10/442,000	Cleaning Compositions and Method of	Wai Mull Lee	03/20/2003	00937-109-03	8317-189-999
10/630,300	Use Thereof	Wai Mun Lee	07/30/2003	60937-194-US	9317 104 000
10/030,300	Compositions and Methods for	VV al IVIUIT LEE	07/30/2003	00937-194-03	8317-194-999
	Rapidly Removing Overfilled				
60/518,337	Substrates	Chelle, et al.	11/10/2003	60937-200-PR	0247 200 000
00/310,337	CMP Method for Copper, Tungsten,	Crielle, et al.	11/10/2003	00937-200-PR	8317-200-888
	Titanium, Polysilicon, and Other		•		
	Substrates Using Organosulfonic				
10/690,623	Acids as Oxidizers	Carter, et al.	10/23/2003	60937-202-US	8317-202-999
10/030,023	PeriodicAcid Compositions for	Carter, et al.	10/23/2003	00937-202-03	0317-202-333
	Polishing Nobel Metal/High K	٠.			
60/494,954	Substrates	Robert J. Small	08/14/2003	60937-203-PR	8317-203-888
00/797,907	Cerium Oxide Abrasives for Chemical	Nobell J. Ollian	00/14/2003	00937-203-FK	0317-203-000
60/509,920	Mechanical Polishing	Robert J. Small	10/10/2003	60937-204-PR	8317-204-888
00/000,020	W.Ooriamoan Chorming	roborto. Oman	10/10/2000	00337-204-110	0317-204-000
	Chemical Mechanical Polishing				
	Slurries and Cleaners Containing				
60/516.736	Salicyclic Acid as a Corrosion Inhibitor	Carter, et al.	11/04/2003	60937-206-PR	8317-206-888
00,010,100	Periodic Acid Compositions for	ourior, or an	1170172000	00001 200111	0011 200 000
60/494,955	Polishing Ruthenium Substrates	Robert J. Small	08/14/2003	60937-207-PR	8317-207-888
	Chemical Mechanical Polishing		567 1 112000	00001 207 110	0011 201 000
10/683,730	Compositions and Process	Small, et al.	10/10/2003	60937-211-US	8317-211-999
10,000,100	Alumia Abrasive for Chemical	Oman, or an	1011012000	00001 211 00	0011 211 000
60/514,020	Mechanical Polishing	Philippe H. Chelle	10/27/1999	60937-213-PR	8317-213-888
		pps 57.55	10/2//1000	00001 210111	
	Chemical Mechanical Polishing				
	Slurries and Cleaners Containing				
60/502,951	Salicyclic Acid as a Corrosion Inhibitor	Tamilmani, et al.	09/16/2003	60937-214-PR	8317-214-888
	Compositions for Chemical				
	Mechanical Planarization of Tantalum				
10/665,417	and Tantalum Nitride	Small, et al.	09/22/2003	60937-215-US	8317-215-999
	Alumina Abrasive for Chemical				
60/526,107	Mechanical Polishing	Chelle, et al.	12/02/2003	60937-216-PR	8317-216-888
	Particulate or Particle-Bound				
60/509,922	Chelating Agents	Small, et al.	10/10/2003	60937-217-PR	8317-217-888
	Particulate or Particle-Bound				
10/690,626	Chelating Agents	Small, et al.	10/23/2003	60937-217-US	8317-217-999
	Chemical Mechanical Polishing of STI		,		
	Features on Semiconductors: Water				
60/533,054	Polishing with Ceria Slurries	Yu, et al.	12/30/2003	60937-223-PR	8317-223-888
	Removal of Post Etch Residues and				į
	Copper Contamination From Low-K				
	Dielectrics Using Superciritcal CO2				İ
60/511,949	with Diketone Additives	Jerome Daviot	10/14/2003	60937-225-PR	8317-225-888
	Method and Apparatus for Substrate	• -			
10/694,999	Pre-Treatment	Lee, et al.	10/29/2003	60937-226-US	8317-226-999

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	Method of Chemically Mechanically				
60/515,450	Polishing Substrates	Brandon S. Scott	10/30/2003	60937-228-PR	8317-228-888